

Analysis of Porous Silicon Size in Raman Scattering

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The Raman scattering was studied from the porous silcons which were made by changing anodization current and time. As the current density was increased, it was observed that Raman peak was red shift and the full width half maximum increased, and was analyzed theoretically.

Key words : porous silicon, Raman scattering

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가

Phonon
(non-radiative transition)

가

Tsu

(Tsu et al., 1992). Z. Sui

가

480 cm⁻¹ 가

(1990) 가 Canham , p

HF 2.5 3 nm

(Sui et al., 1992).

가

500 800nm

가 PL (photoluminescence) 가

H. Muender 36 65%
 가 가
 35 가 가
 , 가
 (Muender et al.,
 1992). A. Halimaoui 가 가 p p+

(Gregoria et al., 1994).

p

가

가 520 cm⁻¹
 가

가

II.

(q = 0) (Brillouin zone)
 (point)

가

520 cm⁻¹

가

35 cm⁻¹
 480 cm⁻¹
 (Morhange

et al., 1979).

가

(phonon confinement model)

가 . Richter (1981)

Campbell (1986)

가

(FWHM: full width at half-
 maximum) 가

maximum)

$$\phi(q_0, r) = u(q_0, r) \exp(-i q_0 \cdot r)$$

q₀ , u(q₀, r)
 (Bloch)

가 , W(r, L),
 L

φ

$$\Psi(q_0, r) = W(r, L)\phi(q_0, r) = u(q_0, r)\Psi'(q_0, r) \quad (1)$$

, Ψ'(q₀, r)
 가

$$\Psi'(q_0, r) = \int C(q_0, q) \exp(iq \cdot r) \quad (2)$$

$$C(q_0, q) = \frac{1}{(2\pi)^3} \int \Psi'(q_0, r) \exp(-q \cdot r) dr \quad (3)$$

가 , W(r, L),
 가 가

$$W(r, L) = \exp(-8\pi^2 r^2 / L^2) \quad (4)$$

L

가

$$|C(q_0, q)|^2 \cong \exp(-q^2 L^2 / 16\pi^2) \quad (5)$$

$$I(\omega) \propto \int_0^{2\pi/a_0} \frac{|C(q_0, q)|^2 4\pi q^2 dq}{[\omega - \omega(q)]^2 + (\Gamma_0/2)^2} \quad (6)$$

$$\omega(q) = \omega_0 - 120(q/q_0) \quad (7)$$

$$\omega_0 = 520 \text{ cm}^{-1}, \quad q_0 = 2\pi/a_0$$

(5) (7)

III.

0.06 0.12 cm p (100)
20 % HF-

가

Fig. 1 Canham (1990)

HF-
0.49 cm²

가

Arbitrary Function Generator (Houkuto Denko Ltd., HB-105)

가

Fig. 2
488 nm 20 mW

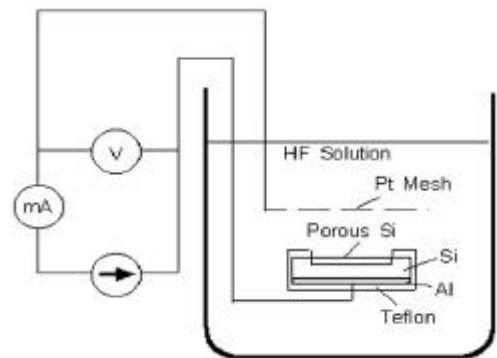


Fig. 1. The apparatus for the formation of porous silicon.

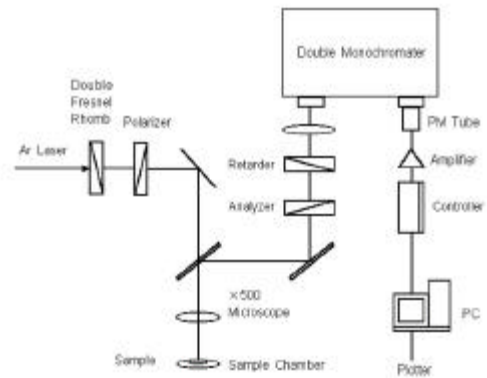


Fig. 2. The experimental setup for measuring the Raman signal.

Fig. 3

Fig. 3(a)
520 cm⁻¹

가

Fig. 3(b)

cm⁻¹ 520 cm⁻¹ (FWHM) 7.9
2.5 cm⁻¹
가 40 mA/cm²

가 500 가
 가
 가 10 가
 (resonance effect)
 (Cardona and Guntherodt, 1984)
 (surface enhancement) (Cardona and Guntherodt, 1982)
 가 가
 가
 가 520 cm⁻¹

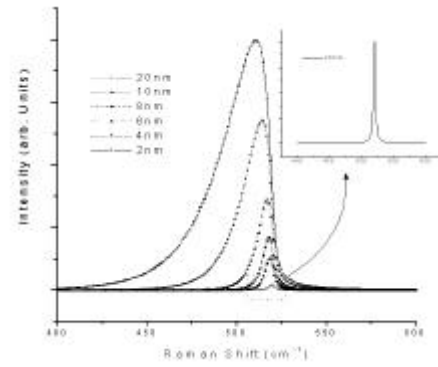


Fig. 4. The Raman spectra of computer simulation.

Fig. 4
 ±0.1
 nm, ±0.5 cm⁻¹, ±0.5 cm⁻¹

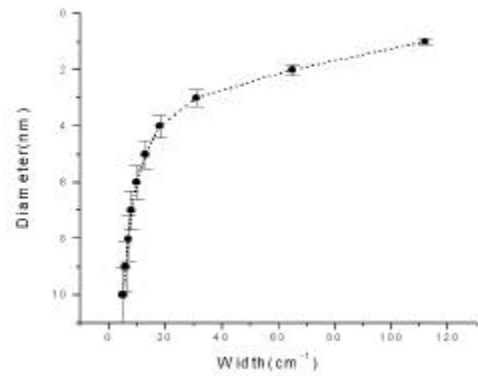


Fig. 5. The relationship between the peak width and the crystal diameter.

Fig. 5
 10
 nm

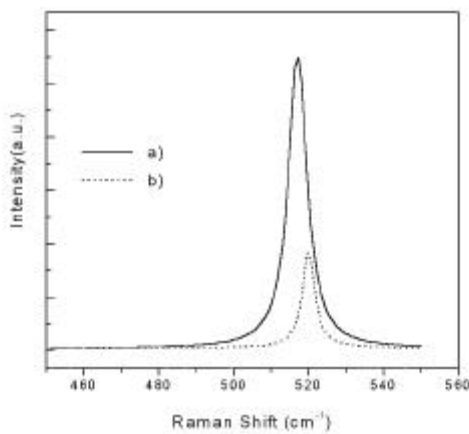


Fig. 3. The Raman spectra of light-emitting porous silicon samples.
 a) porous silicon; 40 mA/cm², 500 sec
 b) p-type single crystalline silicon wafer.

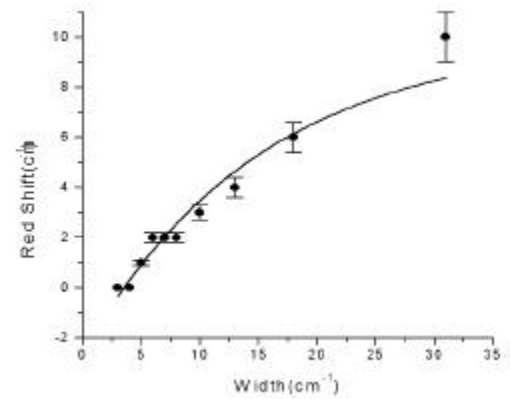


Fig. 6. The relationship between the peak width and the red shift.

IV.

20% HF-
가
가

가 가
520 cm⁻¹

가

가

가 PL

가

V.

1997

VI.

1996. 36(5): 856.

1995.
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